

PRODUCT / PROCESS CHANGE NOTIFICATION

1. PCN basic data

1.1 Company	 STMicroelectronics International N.V
1.2 PCN No.	POWER AND DISCRETES/26/16536
1.3 Title of PCN	HU3PAK SiC MOSFET Gen 3: Back End introduction at Bouskoura (BSK) _ Morocco on top of the actual ATJ JAPAN on new 8 inches Front End FABs with wire bonding optimization.
1.4 Product Category	Pls Refer to the impacted Product list. (BBRF7A1, BRI9A1, BVJ7A1/BRJ7A1)
1.5 Issue date	2026-08-07

2. PCN Team

2.1 Contact supplier	
2.1.1 Name	PIKE EMMA
2.1.2 Phone	+44 1628896111
2.1.3 Email	emma.pike@st.com
2.2 Change responsibility	
2.2.1 Product Manager	Angelo RAO
2.1.2 Marketing Manager	Francesco FISICHELLA
2.1.3 Quality Manager	Massimiliano CUOZZO

3. Change

3.1 Category	3.2 Type of change	3.3 Manufacturing Location
Transfer	Product transfer from one site to another site, even if test or process line is qualified	- CW8F/SiC Campus and SSTF/Sanan as Front End Plants - ATJ/Japan and BSK/Marocco as Back End Plants

4. Description of change

	Old	New
4.1 Description	HU3PAK production - CTWF/Catania FE 6" as Front End Plant - ATJ/Japan BE Plant - Source Wire Bonding diagram 2x10mils or 4x7mils	HU3PAK production - CW8F/SiC Campus and SSTF/Sanan as Front End Plants - BSK/Marocco - Source Wire Bonding diagram 4x10mils
4.2 Anticipated Impact on form,fit, function, quality, reliability or processability?	No Impact	

5. Reason / motivation for change

5.1 Motivation	Capacity Extension
5.2 Customer Benefit	SERVICE CONTINUITY

6. Marking of parts / traceability of change

6.1 Description	by FGs
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7. Timing / schedule

7.1 Date of qualification results	2027-01-15
7.2 Intended start of delivery	2027-01-29
7.3 Qualification sample available?	Upon Request

8. Qualification / Validation

8.1 Description			
8.2 Qualification report and qualification results	In progress	Issue Date	

9. Attachments (additional documentations)		
16536 Public product.pdf 16536 HU3PAK - BSK introduction in 8 inches manufacturing locations.pdf 16536 HU3PAK_BSK BE introduction and BSK_ATJ source wire bonding optimization for 8 inches_Rev3 2.pdf		
10. Affected parts		
10. 1 Current		10.2 New (if applicable)
10.1.1 Customer Part No	10.1.2 Supplier Part No	10.1.2 Supplier Part No
4632681	SCT040HU120G3AG	

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Public Products List

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PCN Title : HU3PAK_SiC MOSFET Gen 3: Back End introduction at Bouskoura (BSK) _ Morocco on top of the actual ATJ JAPAN on new 8 inches Front End FABs with wire bonding optimization.

PCN Reference : POWER AND DISCRETES/26/16536

Subject : Public Products List

Dear Customer,

Please find below the Standard Public Products List impacted by the change.

SCT040HU120G3AG	SCT040HU65G3AG	SCT070HU120G3AG
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HU3PAK_BSK BE introduction and BSK/ATJ source wire bonding optimization for 8 inches GEN3 Technology Reliability Plan

Analog, Power & Discrete, MEMS & Sensors Group

Quality & Reliability

July 2026

Reliability Plan Strategy

In the next slides we reported the reliability plan for the HU3PAK package to be introduced at BSK and source wire bonding optimization for both BSK and ATJ.

- The product will be qualified according to the latest international guideline AEC-Q101 rev.E, and ST internal specification #0061692
- Three different assembly lots are required for the representative test vehicles.
- The strategy is based on the following:

BRJ9A1 requires a delta reliability matrix to evaluate new source wire bonding optimization for all combinations WSiC/BSK, WSiC/ATJ, JV-Sanan/BSK and JV-Sanan/ATJ.

BRJ7A1/BVJ7A1 was selected to evaluate source wire bonding optimization for the JV-Sanan/BSK and JV-Sanan/ATJ combinations

BRF7A1 was chosen to evaluate source wire bonding optimization for the WSiC/BSK and WSiC/ATJ combinations

Products involved

BSK introduction and BSK source wire bonding optimization

CP	Product Line	Diffusion Fab	Reliability Strategy
SCT040HU65G3AG	BRF7A1	JV-SANAN	DERIVATIVE
SCT070HU120G3AG	BRJ7A1-BVJ7A1	JV-SANAN	Delta Evaluation
SCT040HU120G3AG	BRI9A1	JV-SANAN	Delta Evaluation
SCT040HU65G3AG	BRF7A1	WSiC	Delta Evaluation
SCT070HU120G3AG	BRJ7A1-BVJ7A1	WSiC	DERIVATIVE
SCT040HU120G3AG	BRI9A1	WSiC	Delta Evaluation

ATJ source wire bonding optimization

CP	Product Line	Diffusion Fab	Reliability Strategy
SCT040HU65G3AG	BRF7A1	JV-SANAN	DERIVATIVE
SCT070HU120G3AG	BRJ7A1-BVJ7A1	JV-SANAN	Delta Evaluation
SCT040HU120G3AG	BRI9A1	JV-SANAN	Delta Evaluation
SCT040HU65G3AG	BRF7A1	WSiC	Delta Evaluation
SCT070HU120G3AG	BRJ7A1-BVJ7A1	WSiC	DERIVATIVE
SCT040HU120G3AG	BRI9A1	WSiC	Delta Evaluation



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Trials detail for products diffused to **JV Sanan** with **ATJ** as assembly plant

Reliability Test Item	Test Condition	BRI9A1 HU3PAK	BRF7A1 HU3PAK	BVJ7A1 – BRJ7A1 HU3PAK	Family Data			
					BVJJA1 HU3PAK	BRGNA1 H2PAK-7	BRGNA1 STPAK	BRJO TO247-4
Parametric Verification	All parameters according to user specification	25 x 1 Lots	25 x 1 lot	25 x 1 lot	25 x1	25 x 3 Lots	25 x 3 Lots	25 x 3Lots
Preconditioning	24h bake@125°C MSL1: 168h moisture soak @ TA=85°C, RH=85% 3x Reflow simulation with Peak Reflow Temp= 245°C	ALL parts submitted to TC, IOL, H3TRB and AC	ALL parts submitted to TC, IOL, H3TRB and AC	Fam. Data BRF7A1	ALL parts submitted to TC, IOL, H3TRB and AC	ALL parts submitted to TC, IOL, H3TRB and AC	ALL parts submitted to TC, IOL, H3TRB and AC	NA
HTRB	1000h @ Ta=175°C, Vds= 750V (BRGN) 1000h @ Ta=175°C, Vds= 650V (BRFx) 1000h @ Ta=175°C, Vds= 1200V (BVJx/BRix)	Fam Data BRJOA1 TO247-4	77 x 1 Lot Fam. Data BRGNA1	Fam. Data BRJOA1 TO247-4	-	77 x 3 lots	77 x 3 lots	77 x 3 lots
HTGB	HTGB+ Tj=175°C, Vgs= 22V, 1000h	Fam Data BRJOA1 TO247-4	77 x 1 Lot Fam. Data BRGNA1	Fam. Data BRJOA1 TO247-4	-	77 x 1 lot	77 x 3 lots	77 x 3 lots
	HTGB- Tj=175°C, Vgs= -10V, 1000	Fam Data BRJOA1 TO247-4	77 x 1 Lot Fam. Data BRGNA1	Fam. Data BRJOA1 TO247-4	-	77 x 1 lot	77 x 3 lots	77 x 3 lots
TC	Ta=-55°C /+150°C Duration= 1000cy	77 x 3 assy Lots	77 x 3 Lots	Fam.Data BRF7A1 HU3PAK	77 x 3 lots	77 x 3 lots	77 x 3 lots	77 x 3 lots
AC	Autoclave (Ta=121°C, Pa=2atm for 96 hours)	Fam.Data BVJJA1 HU3PAK	Fam.Data BVJJA1 HU3PAK	Fam.Data BVJJA1 HU3PAK	77 x 3 lots	77 x 3 lots	77 x 3 lots	77 x 3 lots
HV H3TRB	1000h @ Ta=85°C, RH=85% 80% Vdsmax	77 x 3 assy Lots	77 x 3 Lots	Fam.Data BRF7A1 HU3PAK	77 x 3 lots	77 x 3 lots	77 x 3 lots	77 x 3 lots
IOL	15Kcy / ΔTj ≥ 100°C	77 x 3 assy Lots	77 x 3 Lots	Fam.Data BRF7A1 HU3PAK	77 x 3 lots	77 x 3 lots	77 x 3 lots	77 x 3 lots
ESD	ESD HBM/CDM Characterization	1 Lots	1 Lots	1 Lots	1 Lots	1 Lots	1 Lot	1 Lot
DPA	Devices after TC and H3TRB	1 Lot	1 Lot	1 Lot	1 Lot	1 Lot	1 Lot	1 Lot

Trials detail for products diffused to JV Sanan with BSK as assembly plant

Reliability Test Item	Test Condition	BRI9A1 HU3PAK	BRF7A1 HU3PAK	BVJ7A1 – BRJ7A1 HU3PAK	Family Data		
					BRGNA1 H2PAK-7	BRGNA1 STPAK	BRJO TO247-4
Parametric Verification	All parameters according to user specification	25 x 1 Lots	25 x 1 lot	25 x 1 lot	25 x 3 Lots	25 x 3 Lots	25 x 3Lots
Preconditioning	24h bake@125°C MSL1: 168h moisture soak @ TA=85°C, RH=85% 3x Reflow simulation with Peak Reflow Temp= 245°C	ALL parts submitted to TC, IOL, H3TRB and AC	ALL parts submitted to TC, IOL, H3TRB and AC	ALL parts submitted to TC, IOL, H3TRB + Fam.Data BRI9	ALL parts submitted to TC, IOL, H3TRB and AC	ALL parts submitted to TC, IOL, H3TRB and AC	NA
HTRB	1000h @ Ta=175°C, Vds= 750V (BRGN) 1000h @ Ta=175°C, Vds= 650V (BRFx) 1000h @ Ta=175°C, Vds= 1200V (BVJx/BRlx)	77 x 1 Lot + Fam Data BRJOA1 TO247-4	77 x 1 Lot +Fam. Data BRGNA1 H2PAK-7	77 x 1 Lot + Fam. Data BRJOA1 TO247-4	77 x 3 lots	77 x 3 lots	77 x 3 lots
HTGB	HTGB+ Tj=175°C, Vgs= 22V, 1000h	77 x 1 Lots + Fam Data BRJOA1 TO247-4	77 x 1 lot + Fam. Data BRGNA1 STPAK	77 x 1 lot + Fam. Data BRI9A1 + Fam Data BRJOA1 TO247-4	77 x 1 lot	77 x 3 lots	77 x 3 lots
	HTGB- Tj=175°C, Vgs= -10V, 1000	77 x 1 Lots + Fam Data BRJOA1 TO247-4	77 x 1 lot + Fam. Data BRGNA1 STPAK	77 x 1 lot + Fam. Data BRI9A1 + Fam Data BRJOA1 TO247-4	77 x 1 lot	77 x 3 lots	77 x 3 lots
TC	Ta=-55°C /+150°C Duration= 1000cy	77 x 3 assy Lots	Fam. Data BVJ7A1	77 x 3 assy Lots	77 x 3 lots	77 x 3 lots	77 x 3 lots
AC	Autoclave (Ta=121°C, Pa=2atm for 96 hours)	77 x 3 assy Lots	Fam. Data BRI9A1	Fam. Data BRI9A1	77 x 3 lots	77 x 3 lots	77 x 3 lots
HV H3TRB	1000h @ Ta=85°C, RH=85% 80% Vdsmax	77 x 3 assy Lots	Fam. Data BVJ7A1	77 x 3 assy Lots	77 x 3 lots	77 x 3 lots	77 x 3 lots
IOL	15Kcy / ΔTj ≥ 100°C	77 x 3 assy Lots	Fam. Data BVJ7A1	77 x 3 assy Lots	77 x 3 lots	77 x 3 lots	77 x 3 lots
ESD	ESD HBM/CDM Characterization	1 Lots	1 Lots	1 Lots	1 Lots	1 Lot	1 Lot
DPA	Devices after TC and H3TRB	1 Lot	1 Lot	1 Lot	1 Lot	1 Lot	1 Lot

Trials detail for products diffused to WSiC with ATJ as assembly plant

Reliability Test Item	Test Condition	BRI9A1 HU3PAK	BRF7A1 HU3PAK	BVJ7A1 HU3PAK	Family Data	
					BRFCA1 HU3PAK	BVJJA1 HU3PAK
Parametric Verification	All parameters according to user specification	25 x 1 Lots	25 x 1 Lots	25 x 1 Lots	25 x 3 Lots	25 x 1 Lots
Preconditioning	24h bake@125°C MSL1: 168h moisture soak @ TA=85°C, RH=85% 3x Reflow simulation with Peak Reflow Temp= 245°C	Fam.Data BRIGA1 HU3PAK	Fam.Data BRFCA1 + BVJ7A1 HU3PAK	ALL parts submitted to TC, IOL, H3TRB and AC	ALL parts submitted to TC, IOL, H3TRB and AC	ALL parts submitted to TC, IOL, H3TRB and AC
HTRB	1000h @ Ta=175°C, Vds= 750V (BRGN) 1000h @ Ta=175°C, Vds= 650V (BRFx) 1000h @ Ta=175°C, Vds= 1200V (BVJx/BRIx)	Fam.Data BRIGA1 HU3PAK	Fam.Data BRFCA1 HU3PAK	77 x 1 Lot + Fam.Data BVJJA1 HU3PAK	77 x 3 lots	77 x 2 Lot + Fam.Data BVJ7A1 HU3PAK
HTGB	HTGB+ Tj=175°C, Vgs= 22V, 1000h	Fam.Data BRIGA1 HU3PAK	Fam.Data BRFCA1 HU3PAK	77 x 1 Lot + Fam.Data BVJJA1 HU3PAK	77 x 3 lots	77 x 2 Lot + Fam.Data BVJ7A1 HU3PAK
	HTGB- Tj=175°C, Vgs= -10V, 1000	Fam.Data BRIGA1 HU3PAK	Fam.Data BRFCA1 HU3PAK	77 x 1 Lot + Fam.Data BVJJA1 HU3PAK	77 x 3 lots	77 x 2 Lot + Fam.Data BVJ7A1 HU3PAK
TC	Ta=-55°C /+150°C Duration= 1000cy	77 x 3 assy Lots	Fam.Data BRFCA1 + BVJ7A1 HU3PAK	77 x 3 assy Lots	77 x 3 lots	77 x 2 Lot + Fam.Data BVJ7A1 HU3PAK
AC	Autoclave (Ta=121°C, Pa=2atm for 96 hours)	Fam.Data BRIGA1 HU3PAK	Fam.Data BRFCA1 + BVJ7A1 HU3PAK	77 x 3 assy Lots	77 x 3 lots	77 x 2 Lot + Fam.Data BVJ7A1 HU3PAK
HV H3TRB	1000h @ Ta=85°C, RH=85% 80% Vdsmax	77 x 3 assy Lots	Fam.Data BRFCA1 + BVJ7A1 HU3PAK	77 x 3 assy Lots	77 x 3 lots	77 x 2 Lot + Fam.Data BVJ7A1 HU3PAK
IOL	15Kcy / ΔTj ≥ 100°C	77 x 3 assy Lots	Fam.Data BRFCA1 + BVJ7A1 HU3PAK	77 x 3 assy Lots	77 x 3 lots	77 x 2 Lot + Fam.Data BVJ7A1 HU3PAK
ESD	ESD HBM/CDM Characterization	1 Lots	1 Lots	1 Lots	1 Lots	1 Lots
DPA	Devices after TC and H3TRB	1 Lot	Fam.Data BVJ7A1 HU3PAK	1 Lot	1 Lot	1 Lot

Trials detail for products diffused to WSiC with BSK as assembly plant

Reliability Test Item	Test Condition	BRI9A1 HU3PAK	BRF7A1 HU3PAK	BVJ7A1 HU3PAK	Family Data	
					BRFGA1 HU3PAK	BVJJA1 HU3PAK
Parametric Verification	All parameters according to user specification	25 x 1 Lots	25 x 1 Lots	25 x 1 Lots	25 x 3 Lots	
Preconditioning	24h bake@125°C MSL1: 168h moisture soak @ TA=85°C, RH=85% 3x Reflow simulation with Peak Reflow Temp= 245°C	ALL parts submitted to TC, IOL, H3TRB and AC Fam.Data BVJ7A1 + BVJJA1 HU3PAK	Fam.Data BVJ7A1 HU3PAK	ALL parts submitted to TC, IOL, H3TRB and AC	ALL parts submitted to TC, IOL, H3TRB and AC	ALL parts submitted to TC, IOL, H3TRB and AC
HTRB	1000h @ Ta=175°C, Vds= 650V (BRFx) 1000h @ Ta=175°C, Vds= 1200V (BRlx/BVJx)	Fam.Data BVJ7A1 + BVJJA1 HU3PAK	Fam.Data BRFGA1 HU3PAK	77 x 1 Lot + Fam.Data BVJJA1 HU3PAK	77 x 3 lots	77 x 2 Lot + Fam.Data BVJ7A1 HU3PAK
HTGB	HTGB+ Tj=175°C, Vgs= 22V, 1000h	Fam.Data BVJ7A1 + BVJJA1 HU3PAK	Fam.Data BRFGA1 HU3PAK	77 x 1 Lot + Fam.Data BVJJA1 HU3PAK	77 x 3 lots	77 x 2 Lot + Fam.Data BVJ7A1 HU3PAK
	HTGB- Tj=175°C, Vgs= -10V, 1000	Fam.Data BVJ7A1 + BVJJA1 HU3PAK	Fam.Data BRFGA1 HU3PAK	77 x 1 Lot + Fam.Data BVJJA1 HU3PAK	77 x 3 lots	77 x 2 Lot + Fam.Data BVJ7A1 HU3PAK
TC	Ta=-55°C /+150°C Duration= 1000cy	77 x 3 assy Lots	Fam.Data BVJ7A1 HU3PAK	77 x 3 assy Lots	77 x 3 lots	77 x 2 Lot + Fam.Data BVJ7A1 HU3PAK
AC	Autoclave (Ta=121°C, Pa=2atm for 96 hours)	Fam.Data BVJ7A1 + BVJJA1 HU3PAK	Fam.Data BVJ7A1 HU3PAK	77 x 3 assy Lots	77 x 3 lots	77 x 2 Lot + Fam.Data BVJ7A1 HU3PAK
HV H3TRB	1000h @ Ta=85°C, RH=85% 80% Vdsmax	77 x 3 assy Lots	Fam.Data BVJ7A1 HU3PAK	77 x 3 assy Lots	77 x 3 lots	77 x 2 Lot + Fam.Data BVJ7A1 HU3PAK
IOL	15Kcy / ΔTj ≥ 100°C	77 x 3 assy Lots	Fam.Data BVJ7A1 HU3PAK	77 x 3 assy Lots	77 x 3 lots	77 x 2 Lot + Fam.Data BVJ7A1 HU3PAK
ESD	ESD HBM/CDM Characterization	1 Lots	1 Lots	1 Lots	1 Lots	1 Lots
DPA	Devices after TC and H3TRB	1 Lot	Fam.Data BVJ7A1 HU3PAK	1 Lot	1 Lot	1 Lot

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Product/process change notification:
 HU3PAK_SiC MOSFET Gen 3: Back End introduction at Bouskoura (BSK) – Morocco and Back End source wire bonding optimization (both ATJ-Japan and BSK-Morocco) on new 8 inches Front End FABs.

POWER AND DISCRETES/26/16536

Product family	Technology	Package
SiC MOSFET	Gen 3	HU3PAK

Description of the change

Dear Customer,

Following the continuous improvement of our service and in order to increase the productivity, this document is announcing that SiC MOSFETs, listed in this PCN, diffused at 8 inch and assembled in HU3PAK package at ATJ-Japan Plant, will be also assembled in Bouskoura (BSK) – Morocco ST Plant.

HU3PAK produced in BSK guarantees the same quality and performance as per current production.

BSK is a Back-End manufacturing facility that has been extensively utilized to produce ST IGBT, High-Voltage Silicon MOSFET, and Silicon Carbide custom products for several years.

Furthermore, a wire bonding optimization will be implemented across both Back-End facilities (ATJ and BSK) to ensure compliance with newly stringent application requirements.

Here below a table listing the impacted Commercial Products:

CP
SCT040HU65G3AG
SCT070HU120G3AG
SCT040HU120G3AG

Product/process change notification:

HU3PAK_SiC MOSFET Gen 3: Back End introduction at Bouskoura (BSK) – Morocco
and Back End source wire bonding optimization (both ATJ-Japan and BSK-Morocco) on
new 8 inches Front End FABs

POWER AND
DISCRETES/26/16536

Reason
Capacity extension / service improvement

Date of implementation
Starting from Jan, 29 th 2027

Qualification of the change
See attached Qualification Plan

Marking and traceability:

Unless otherwise stated by customer specific requirement, traceability of products affected by these changes will be ensured by Finished Good.

Sincerely Yours.

Catania, Aug 5th 2026

Product/process change notification:

H HU3PAK SiC MOSFET Gen 3: Back End introduction at Bouskoura (BSK) – Morocco
and Back End source wire bonding optimization (both ATJ-Japan and BSK-Morocco) on
new 8 inches Front End FABs

POWER AND
DISCRETES/26/16536

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